

Corrigendum: Analysing black phosphorus transistors using an analytic Schottky barrier MOSFET model

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This Article contains an error in the penultimate sentence of the penultimate paragraph. This sentence should read: ‘In other words, if one would analyse the minimum current level I_{\min} using a simple parabolic $\kappa(E)$ WKB approximation, one would extract a much smaller bandgap since I_{\min} is severely underestimated.’



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